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PTO/SB/08A (08-00)

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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 2

of 2

Complete if Known

Application Number	10/064,232
Filing Date	June 24, 2002
First Named Inventor	Jason R. Jenny et al.
Group Art Unit	1765
Examiner Name	Matthew A. Anderson
Attorney Docket Number	5000.236

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MAA	4	S.K. LILOV; <i>Determination of native defect concentrations and deviation from stoichiometry in silicon carbide</i> ; Materials Science & Engineering; April 15, 1993; pages 226-229; Vol. B18, No. 3; Switzerland	
MAA	5	YOH-ICHI YAMAGUCHI ET AL.; <i>Properties of heteroepitaxial 3C-SiC films grown by LPCVD</i> ; Sensors and Actuators A; June 1, 1996; pages 695-699, Vol. 54, No. 1-3; Elsevier Sequoia S.A.; Lausanne, CH	
MAA	6	A. ELLISON ET AL.; <i>HTCVD growth of semi-insulating 4H-SiC crystals with low defect density</i> ; Silicon Carbide-Materials, Processing and Devices Symposium (Materials Research Society Symposium Proceedings Vol. 640) Silicon Carbide-Materials, Processing and Devices Symposium, Boston, MA, USA, 27-29, Nov. 2000, 2001 Warrendale, PA, USA, Mater. Res. Soc., USA, pages H1.2.1 - 11	
MAA	7	VIKTOR V. ZELENIN ET AL.; <i>Growth and investigation of epitaxial 6H-SiC layers obtained by CVD on Lely-grown substrates</i> ; Materials Science and Engineering B; April 1, 1997; pages 300-303; Vol. 46, No. 1-3; Elsevier Sequoia, Lausanne, CH	
MAA	8	SVITLANA I. VLASKINA ET AL.; <i>6H to 3C Polytype Transformation in Silicon Carbide</i> ; Japanese Journal of Applied Physics, Part 2 (Letters); January 15, 1999; pages L27-L29; Vol. 38, No. 1A-B; Publication Office, Japanese Journal Appl. Phys.; Japan	

Examiner
Signature

Matthew A. Anderson

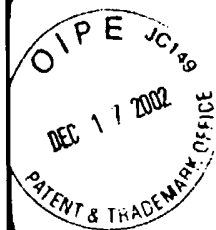
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6/23/04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.

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Electronic Information Disclosure Statement

Method For Producing Semi-Insulating Resistivity In High Purity Silicon Carbide Crystals

Application:



10/064232

Confirmation:

6381

Applicant(s):

Jason Jenny

Docket Number:

5000.236

Group Art Unit:

1765

Examiner:

search string: (6218680 or 4866005 or 6403982 or 6396080 or 20010017374 or 20020167010).pn.

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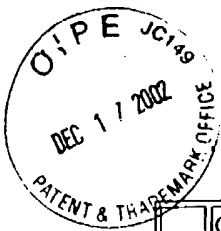
US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents



init	Citation No.	Patent Number	Date	Bar Code	Patentee	Class	Subclass
MA	P01	6218680	2001-04-17		Carter	257	77
MA	P02	4866005	1989-09-12		Davis	437	100
MA	P03	6403982	2002-06-11		Carter	257	77
MA	P04	6396080	2002-05-28		Carter	257	77

Matthew Anderson 6/24/04

Published Applications



Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Citation No.	Patent Number	Date	Bar Code	Patentee	Class	Subclass
<i>MA</i>	U01	20010017374	2001-08-30		Carter	257	78
<i>MA</i>	U02	20020167010	2002-11-14		Mueller	257	77

Signature

Examiner Name	Date
<i>Matthew Anderson</i>	<i>6/24/04</i>

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